L Number	Hits	Search Text	DB	Time stamp
-	2	6251488.pn. 6288442.pn.	USPAT; US-PGPUB	2004/07/22 09:11
-	7196	438/637.ccls. 438/641.ccls. 438/667.ccls. 438/675.ccls. 438/678.ccls. 438/686.ccls. 427/97.ccls. 427/110.ccls. 427/125.ccls. 427/191.ccls. 427/192.ccls. 427/236.ccls. 427/383.1.ccls. 427/422.ccls. 427/455.ccls. 427/597.ccls.	USPAT; US-PGPUB	2004/07/22 09:16
-	1943	(438/637.ccls. 438/641.ccls. 438/667.ccls. 438/675.ccls. 438/678.ccls. 438/686.ccls. 427/97.ccls. 427/110.ccls. 427/125.ccls. 427/191.ccls. 427/192.ccls. 427/236.ccls. 427/383.1.ccls. 427/422.ccls. 427/455.ccls. 427/597.ccls.) and (aerosol spray$6 nanoparticle)	USPAT; US-PGPUB	2004/07/22 09:25
-	663	((438/637.ccls. 438/641.ccls. 438/667.ccls. 438/675.ccls. 438/678.ccls. 438/686.ccls. 427/97.ccls. 427/110.ccls. 427/125.ccls. 427/191.ccls. 427/192.ccls. 427/236.ccls. 427/383.1.ccls. 427/422.ccls. 427/455.ccls. 427/597.ccls.) and (aerosol spray$6 nanoparticle)) and (integrated semiconductor memory cell)	USPAT; US-PGPUB	2004/07/22 09:26
-	453	(((438/637.ccls. 438/641.ccls. 438/667.ccls. 438/675.ccls. 438/678.ccls. 438/686.ccls. 427/97.ccls. 427/110.ccls. 427/125.ccls. 427/191.ccls. 427/192.ccls. 427/236.ccls. 427/383.1.ccls. 427/422.ccls. 427/455.ccls. 427/597.ccls.) and (aerosol spray$6 nanoparticle)) and (integrated semiconductor memory cell)) and (via hole opening plug seed)	USPAT; US-PGPUB	2004/07/22 09:23
-	239	(((438/637.ccls. 438/641.ccls. 438/667.ccls. 438/675.ccls. 438/678.ccls. 438/686.ccls. 427/97.ccls. 427/110.ccls. 427/125.ccls. 427/191.ccls. 427/192.ccls. 427/236.ccls. 427/383.1.ccls. 427/422.ccls. 427/455.ccls. 427/597.ccls.) and (aerosol spray$6 nanoparticle)) and (integrated semiconductor memory cell)) and ((via hole opening plug seed) with (conduct$6 copper cu silver ag gold au))	USPAT; US-PGPUB	2004/07/22 09:24
-	759	(438/637.ccls. 438/641.ccls. 438/667.ccls. 438/675.ccls. 438/678.ccls. 438/686.ccls. 427/97.ccls. 427/110.ccls. 427/125.ccls. 427/191.ccls. 427/192.ccls. 427/236.ccls. 427/383.1.ccls. 427/422.ccls. 427/455.ccls. 427/597.ccls.) and ((aerosol spray$6 nanoparticle) same (conduct$6 copper cu silver ag gold au))	USPAT; US-PGPUB	2004/07/22 09:28
-	323	((438/637.ccls. 438/641.ccls. 438/667.ccls. 438/675.ccls. 438/678.ccls. 438/686.ccls. 427/97.ccls. 427/110.ccls. 427/125.ccls. 427/191.ccls. 427/192.ccls. 427/236.ccls. 427/383.1.ccls. 427/422.ccls. 427/455.ccls. 427/597.ccls.) and ((aerosol spray$6 nanoparticle) same (conduct$6 copper cu silver ag gold au))) and (integrated semiconductor memory cell)	USPAT; US-PGPUB	2004/07/22 12:17
-	465	(438/637.ccls. 438/641.ccls. 438/667.ccls. 438/675.ccls. 438/678.ccls. 438/686.ccls. 427/97.ccls. 427/110.ccls. 427/125.ccls. 427/191.ccls. 427/192.ccls. 427/236.ccls. 427/383.1.ccls. 427/422.ccls. 427/455.ccls. 427/597.ccls.) and ((aerosol spray$6 nanoparticle) with (conduct$6 copper cu silver ag gold au))	USPAT; US-PGPUB	2004/07/22 09:26
-	192	((438/637.ccls. 438/641.ccls. 438/667.ccls. 438/675.ccls. 438/678.ccls. 438/686.ccls. 427/97.ccls. 427/110.ccls. 427/125.ccls. 427/191.ccls. 427/192.ccls. 427/236.ccls. 427/383.1.ccls. 427/422.ccls. 427/455.ccls. 427/597.ccls.) and ((aerosol spray$6 nanoparticle) with (conduct$6 copper cu silver ag gold au))) and (integrated semiconductor memory cell)	USPAT; US-PGPUB	2004/07/22 09:30
-	6486	(aerosol spray$6 nanoparticle) same (conduct$6 copper cu silver ag gold au) same (via hole opening plug seed)	USPAT; US-PGPUB	2004/07/22 09:33
-	1403	(aerosol spray$6 nanoparticle) with (conduct$6 copper cu silver ag gold au) with (via hole opening plug seed)	USPAT; US-PGPUB	2004/07/22 09:29

-	1288	(aerosol spray$6) with (conduct$6 copper cu silver ag gold au) with (via hole opening plug seed)	USPAT; US-PGPUB	2004/07/22 09:29
-	657	((aerosol spray$6 nanoparticle) with (conduct$6 copper cu silver ag gold au) with (via hole opening plug seed)) and (integrated semiconductor memory cell)	USPAT; US-PGPUB	2004/07/22 09:34
-	520	((aerosol spray$6 nanoparticle) same (conduct$6 copper cu silver ag gold au) same (via hole opening plug seed)) same (integrated semiconductor memory cell)	USPAT; US-PGPUB	2004/07/22 09:31
-	274	((aerosol spray$6 nanoparticle) same (conduct$6 copper cu silver ag gold au) same (via hole opening plug seed)) same (memory cell)	USPAT; US-PGPUB	2004/07/22 09:31
-	7426	(aerosol spray$6 nanoparticle) and (conduct$6 copper cu silver ag gold au) and (via hole opening plug seed)	EPO; JPO; DERWENT; IBM_TDB	2004/07/22 09:34
-	509	((aerosol spray$6 nanoparticle) and (conduct$6 copper cu silver ag gold au) and (via hole opening plug seed)) and (integrated semiconductor memory cell)	EPO; JPO; DERWENT; IBM_TDB	2004/07/22 09:35
-	1641	(aerosol spray$6 nanoparticle) same (conduct$6 copper cu silver ag gold au) same (via hole opening plug seed)	EPO; JPO; DERWENT; IBM_TDB	2004/07/22 09:35
-	44	(438/637.ccls. 438/641.ccls. 438/667.ccls. 438/675.ccls. 438/678.ccls. 438/686.ccls.) and (427/97.ccls. 427/110.ccls. 427/125.ccls. 427/191.ccls. 427/192.ccls. 427/236.ccls. 427/383.1.ccls. 427/422.ccls. 427/455.ccls. 427/597.ccls.)	USPAT; US-PGPUB	2004/07/22 09:35
-	85	((aerosol spray$6 nanoparticle) with (conduct$6 copper cu silver ag gold au) with (via hole opening plug seed)) same (integrated semiconductor memory cell)	USPAT; US-PGPUB	2004/07/22 10:02
-	5	("4389973" | "4582731" | "4714047" | "4848273" | "5328078").PN.	USPAT	2004/07/22 11:37
-	10	5529634.URPN.	USPAT	2004/07/22 11:40
-	153	((aerosol spray$6 nanoparticle) same (conduct$6 copper cu silver ag gold au) same (via hole opening plug seed)) and (integrated semiconductor memory cell)	EPO; JPO; DERWENT; IBM_TDB	2004/07/22 11:54
-	110	((438/637.ccls. 438/641.ccls. 438/667.ccls. 438/675.ccls. 438/678.ccls. 438/686.ccls. 427/97.ccls. 427/110.ccls. 427/125.ccls. 427/191.ccls. 427/192.ccls. 427/236.ccls. 427/383.1.ccls. 427/422.ccls. 427/455.ccls. 427/597.ccls.) and ((aerosol spray$6 nanoparticle) same (conduct$6 copper cu silver ag gold au))) and (((integrated adj circuit) ic semiconductor memory cell) same (via hole opening plug seed))	USPAT; US-PGPUB	2004/07/22 16:00
-	268	(maskless adj mesoscale adj2 (materials deposition)) m3d "m.sup.3d" "m.sup.3 d"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/22 16:04
-	158	((maskless adj mesoscale adj2 (materials deposition)) m3d "m.sup.3d" "m.sup.3 d") and (via plug semiconductor ic (integrated adj circuit))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/22 16:05
-	102	((maskless adj mesoscale adj2 (materials deposition)) m3d "m.sup.3d" "m.sup.3 d") and (via plug semiconductor ic (integrated adj circuit)) and (conduct$6 copper cu silver ag gold au)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/22 17:08
-	1	1998jp-0340264.ap,prai.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/07/22 17:33
-	10	(memory adj (cell circuit array)) same (column with row with (decoder address)) same (sensing adj (circuit amplifier)) same (via plug)	USPAT; US-PGPUB	2004/07/22 17:40

-	2	((memory adj (cell circuit array)) same (column with row with (decoder address)) same (sensing adj (circuit amplifier))) and (plug same ((bit adj line) (word adj line) wordline bitline))	USPAT; US-PGPUB	2004/07/22 17:45
-	5	((memory adj (cell circuit array)) same (column with row with (decoder address)) same (sensing adj (circuit amplifier))) and (interconnect$6 same ((bit adj line) (word adj line) wordline bitline))	USPAT; US-PGPUB	2004/07/22 17:47
-	2619	(memory adj (cell circuit array)) same plug	USPAT; US-PGPUB	2004/07/22 17:48
-	1444	(memory adj (cell circuit array)) with plug	USPAT; US-PGPUB	2004/07/22 17:48
-	370	(memory adj (cell circuit array)) same (plug with dielectric)	USPAT; US-PGPUB	2004/07/22 17:49
-	158	(memory adj (cell circuit array)) with (plug with dielectric)	USPAT; US-PGPUB	2004/07/22 17:49
-	358	((memory adj (cell circuit array)) same (plug with dielectric)) and (438/$.ccls. 257/$.ccls.)	USPAT; US-PGPUB	2004/07/22 17:52
-	153	((memory adj (cell circuit array)) with (plug with dielectric)) and (438/$.ccls. 257/$.ccls.)	USPAT; US-PGPUB	2004/07/22 17:53